IN THE SPECIFICATION:

Page 5, lines 14-15:

A1 Figure 2 is an enlarged fragmentary simplified schematic elevational view of the construction of a wafer;

Page 7, lines 11-17:

A2 The insulating layer 14 may illustratively have a thickness of approximately three (3) microns. The sockets 18 may be completely, or partially, formed through the thickness of approximately three (3) microns in the insulating layer 14. Figure 2 illustratively shows the sockets 18 as extending completely through the thickness of the insulating layer 14. The preferred apparatus 10 of this invention illustratively may etch approximately one hundred angstroms (100 Å) from the surface 12 of the insulating layer 14 in a smooth and even layer and without any pits in the layer.

Page 8, lines 1-11:

SUB B1 The apparatus 10 includes an enclosure 20 which may be formed in part by an electrode 22, an electrode 24 displaced from, but preferably substantially parallel to, the electrode 22 and magnets 26 and 28 disposed in a transverse (preferably substantially perpendicular) relationship to the electrodes 22 and 24. The electrode 22 is disposed in a contiguous but spaced and substantially parallel relationship to the wafer 16 and is movable in position toward or away from

A3

the wafer, as indicated by a double-headed arrow 25. The spacing between the wafer 16 and the electrode 22 may illustratively be in the order of 0.1 - 2mm. A plate 30 extending from the magnet 26 in a substantially parallel and adjacent, but spaced, relationship to the electrode 22 also defines the enclosure 20. A ring 32 extending from the magnet 28 to a position spaced from, but adjacent to, the electrode 24 also defines in part the enclosure 20. The plate 30 and the ring 32 may be considered as electrical conductors.

Page 9, line 17 - page 10, line 5:

A conduit 44 is provided for introducing molecules of an inert gas such as argon into the enclosure 20 from a source 45. The argon molecules pass into the enclosure 20 through the space between the electrode 24 and the ring 32. The argon molecules pass out of the enclosure 20 through the space between the plate 30 and the wafer 16. The argon gas flow through the enclosure 20 may illustratively be at a flow rate of 0.1-50 SCCM at a working pressure of 0.5-5mTorr. The movement of the argon molecules through the enclosure 20 is facilitated by a vacuum pump 47.